

H11GXF Series

Rev.A.1.1

DESCRIPTION:

The H11GXF series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a monolithic silicon zero-crossing photo triac to drive a power triac in a plastic DIP5 package with different lead forming options. The products are widely used in solenoid/valve controls, lighting controls, motor controls, temperature controls, static AC power switches, solid state relays, interfacing microprocessors to 265 V_{AC} peripherals.

MAIN FEATURES

High isolation 5000 Vrms

DC input with triac output

Operating temperature range - 40°C to 85 °C

REACH & RoHS compliance

MSL class 2

HBM: H3A; MM: M4

CQC approved

VDE approved

UL approved

ABSOLUTE MAXIMUM RATINGS (Temperature=25°C)

| Parameter | | Symbol | Value | Unit |
|-----------|---|------------------|---------------------|------|
| Input | Forward Current | I _F | 60 | mA |
| | Peak Forward Current | I _{FP} | 1 ⁷ | A |
| | Reverse Voltage | V _R | 6 | V |
| Output | Repetitive peak off-state voltage | V _{DRM} | 600 | V |
| | Repetitive peak off-state voltage | V _{RRM} | 600 | V |
| | Critical rate of rise of on-state current | di/dt | 70 | A s |
| | On-state RMS Current | H11G0F | I _{T(RMS)} | 0.3 |
| H11G1F | | 0.6 | | |



BDC 1-BDC72-9520472205004 4208001 W6.8.00 W0670TW TC-56006 TW-BDS

Operating Temperature

T_{opr}

ORDERING AND MARKING INFORMATION

MARKING INFORMATION



Characteristics Curves

FIG.1: Forward Current vs. Ambient Temperature

FIG.2: On-state Terminal Current vs. Ambient Temperature 0

FIG.7: On-state Terminal Voltage vs. Ambient Temperature

FIG.8: Normalized Holding Current vs. Ambient Temperature



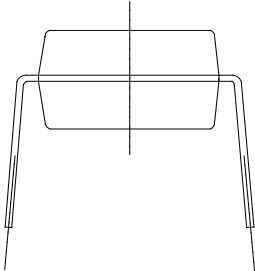
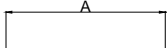
TEST CIRCUITS

FIG.11: Test Circuits of Turn On Time

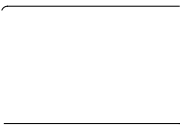
FIG.12: Waveforms of Turn On Time

Package Dimension (Unit: mm)

Standard DIP Type:

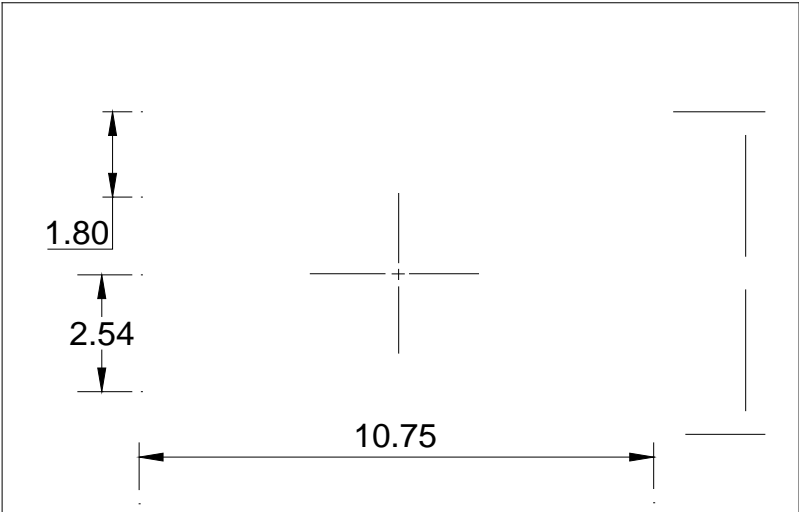


Option SL Type:

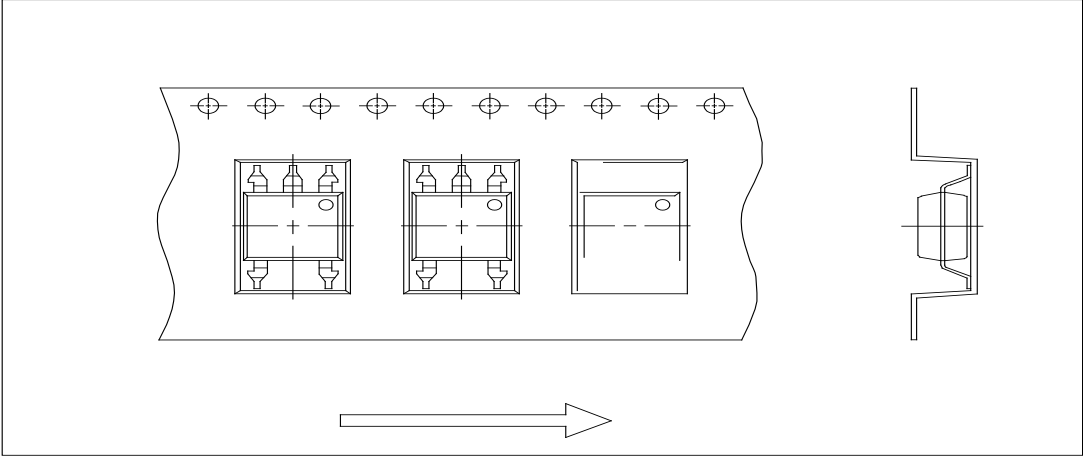


RECOMMENDED SOLDER MASK DIMENSIONS in mm unless otherwise stated)

SL:



Option SLM(T1)



Document Revision History

| Date | Revision | Changes |
|--------------|----------|--------------|
| Feb.21, 2025 | A.1.0 | Last update |
| Nov.7, 2025 | A.1.1 | Add (dV/dt)c |

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